

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	2	US "20070284588" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:25
L5	143	((KINOSHITA near2 YOSHITAKA) or (KAMEI near2 HIDENORI)) and light near emitting	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:28
L6	35	((KINOSHITA near2 YOSHITAKA) or (KAMEI near2 HIDENORI)) and (nitride near4 based) and (light near6 emitting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:29
L7	125	(MATSUSHITA ELECTRIC INDUSTRIAL).asn. and (nitride near4 based) and (light near6 emitting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:35
L8	23	(MATSUSHITA ELECTRIC INDUSTRIAL).asn. and (nitride near4 based) and (light near6 emitting) and third near6 semiconductor (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:37
L9	0	(MATSUSHITA ELECTRIC INDUSTRIAL).asn. and (nitride near4 based) and (light near6 emitting) and third ("n-type" or n type) near6 semiconductor (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:41

L10	8	(nitride near4 based) and (light near6 emitting) and third ("n-type" or n type) near6 semiconductor (layer or film).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:42
L11	2	US "20020179923" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/08/04 15:43
L15	1846	257/E33.068.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/08/04 16:02
L16	113	257/E33.065.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/08/04 16:02
L17	3190	257/288.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/08/04 16:02
S3	1840	(257/213,256,257).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/26 16:03
S4	2708	(257/213,256,257;438/167,186;341/136;331/116,117).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/26 16:05

S28	6	US "6258617" B1	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/26 16:48
S37	2	US "20050133809" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:24
S39	2	US "20030062529" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:25
S40	2	US "20060273327" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:26
S41	2	US "20070096116" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:27
S42	2	US "20050224816" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:27
S43	2	US "20050285128" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:28
S45	12	GaN substrate near10 polish\$3 and substrate near10 etch\$3 and substrate near10 planariz\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:30

S46	0	GaN substrate near10 polish\$3 and substrate near10 etched and substrate near10 planarized and quantum well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:31
S47	0	GaN substrate and InGaN near5 n\$1type semiconductor and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:37
S48	140	GaN substrate and InGaN and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:38
S49	2	GaN substrate and InAlGaIn near10 (n\$1type) and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:40
S50	25	GaN substrate and InAlGaIn and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:40
S53	2	GaN substrate and InAlGaIn and light\$1emitting and aluminum content	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:46
S59	2	InAlGaIn and light\$1emitting and aluminum near10 percentage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:49
S64	2	GaN substrate and InAlGaIn near5 thickness and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 02:52

S65	12	GaN substrate and InAlGaN near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 07:05
S66	1	InAlGaN substrate and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:05
S67	25	InAlGaN near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:07
S68	7	All nGaIn near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:11
S69	2	All nGaIn substrate and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:17
S70	385	257/257.cds.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/06/09 08:22
S71	0	(All nGaIn or InAlGaIn) contact and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:25
S72	0	(All nGaIn or InAlGaIn) contact and light\$1emitting and quantum well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:25

S73	2	(AlInGaN or InAlGaN) contact and light\$1emitting	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:25
S74	73	(AlInGaN or InAlGaN) near5 n\$1type and light\$1emitting	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:28
S75	1	US 2004/0041156 A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:45
S76	3	US "20040041156" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:46
S77	2	US "20020088985" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:48
S78	2	US "20020079506" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:50
S79	1412	(Al near5 In near5 Ga near5 N)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:58
S80	0	(Al near5 In near5 Ga near5 N) substrate and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 08:59

S81	25	(Al near3 In near3 Ga near3 N) and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 09:00
S82	25	(Al near3 In near3 Ga near3 N) and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 09:00
S83	42	(Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 09:03
S84	0	GaN substrate (Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 09:04
S85	17	GaN substrate and (Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/09 09:04
S86	6	US "6462358" B1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/19 16:58
S87	2	US "20070296077" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/06/19 17:13
S88	12	GaN substrate and InAlGaN near5 semiconduct\$3 and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/21 10:15

S89	1	InAlGa _N substrate and light\$1emitting and quantum well near5 thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/21 10:16
S90	220	(Kinoshita near2 Yoshitaka) or (KAMEI near2 HIDEVORI)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/21 10:20
S91	18	((Kinoshita near2 Yoshitaka) or (KAMEI near2 HIDEVORI)) and quantum well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/21 10:20
S92	591	((Hasegawa near2 Yoshiaki) or (Yokogawa near2 Toshiya) or (Ishibashi near2 Akihiko))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/21 11:00
S93	71	((Hasegawa near2 Yoshiaki) or (Yokogawa near2 Toshiya) or (Ishibashi near2 Akihiko)) and nitride and light\$1emitting	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/21 11:01
S94	27	(Al near5 In near5 Ga near5 N) and light\$1emitting and quantum well near5 thickness and diodes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	OFF	2009/01/21 13:52
S95	0	GaN substrate and In adj2 GaN near3 clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 01:01
S96	180	GaN substrate and (InGa _N or InAlGa _N or AlInGa _N) near3 clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 01:02

S97	159	diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near3 clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 01:02
S98	153	light emitting near5 diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near3 clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 01:02
S99	0	light emitting near5 diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near2clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 01:03
S100	52	light emitting near5 diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) near2 clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 01:04
S101	8	light emitting near5 diode and GaN substrate and (InGaN or InAlGaN or AlInGaN) clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 01:13
S102	9	GaN substrate and (InGaN or InAlGaN or AlInGaN) clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 13:16
S103	0	"III-V" near3 Nitride near3 substrate and (InGaN or InAlGaN or AlInGaN) clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 13:22
S104	25	Nitride near3 substrate and (InGaN or InAlGaN or AlInGaN) clad\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/06/19 13:23

S105	23	GaN substrate and (InGaN or InAlGaIn or AlInGaIn or indium) near10 reduce near3 strain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2010/02/27 21:43
S106	3	US "20040207323" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2010/02/27 23:17
S107	0	light emitting diodes and nitride and first near4 layer near "10" ("InGaN" or "AlInGaIn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	OFF	2010/08/14 18:44
S108	7705	light emitting diodes and nitride and first near4 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	OFF	2010/08/14 18:44
S109	1013	light emitting diodes and nitride and first near4 layer same indium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	OFF	2010/08/14 18:45
S110	486	light emitting diodes and nitride same first near4 layer same indium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	OFF	2010/08/14 18:45
S111	8	(light emitting diodes) same nitride same first near4 layer same indium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	OFF	2010/08/14 18:46
S112	2	US "20030022028" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/03/24 20:10

S113	2	US "20100252849" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/03/26 02:26
S114	108	((Konno near2 Taichiroo) or (Tani near2 Takehiko))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/03/26 02:29
S115	1	((Konno near2 Taichiroo) or (Tani near2 Takehiko)) and second reflective	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/03/26 02:30
S116	15	((Konno near2 Taichiroo) or (Tani near2 Takehiko)) and reflective	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2011/03/26 02:30

EAST Search History (Interference)

<This search history is empty>

8/ 4/ 2011 4:02:52 PM

C:\Documents and Settings\vwebb\My Documents\EAST\Workspaces\10593446.wsp